

# 2MBI600VXA-120E-50

**IGBT Modules** 

## **IGBT MODULE (V series)** 1200V / 600A / 2 in one package

#### Features

High speed switching Voltage drive Low Inductance module structure

#### Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



#### Maximum Ratings and Characteristics

Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions	Conditions		Units	
Collector-Emitter voltage	Vces			1200	V	
Gate-Emitter voltage	V <sub>GES</sub>			±20	V	
Collector current	lo.	Continuous	Tc=25°C	800		
	Ic	Continuous	Tc=100°C	600		
	Ic pulse	1ms		1200	Α	
	-lc			600		
	-lc pulse	1ms	1ms			
Collector power dissipation	Pc	1 device	1 device		W	
Junction temperature	Tj		,	175		
Operating junction temperature (under switching conditi	ons) T <sub>jop</sub>				°C	
Case temperature	Tc					
Storage temperature	Tstg					
Isolation voltage between terminal and copper base	(*1) V <sub>iso</sub>	AC : 1min.		4000	VAC	
between thermistor and others (*2)	Viso			4000		
Mounting		M5		6.0		
Screw torque (*3) Main Terminals	-	M8	M8		N m	
Sense Terminals		M4	M4			

Note \*1: All terminals should be connected together during the test.

Note \*2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note \*3: Recommendable Value: Mounting 3.0 ~ 6.0 Nm (M5) Recommendable Value: Main Terminals 8.0 ~ 10.0 Nm (M8)

Recommendable Value: Sense Terminals 1.8 ~ 2.1 Nm (M4)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

ems	Cumbala	Conditions		Characteristics			Units
enis	Symbols Conditions		min.	typ.	max.	Ullits	
Zero gate voltage collector current	Ices	$V_{GE} = 0V, V_{CE} = 1200V$		-	-	4.0	mA
Gate-Emitter leakage current	Iges	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$		-	-	800	nA
Gate-Emitter threshold voltage	V <sub>GE (th)</sub>	$V_{CE} = 20V, I_{C} = 600mA$		6.0	6.5	7.0	V
Collector-Emitter saturation voltage	V <sub>CE</sub> (sat)	V <sub>GE</sub> = 15V I <sub>C</sub> = 600A	Tj=25°C	-	1.85	2.30	V
	(terminal)		Tj=125°C	-	2.15	-	
	(*4)		Tj=150°C	-	2.20	-	
	.,		Tj=25°C	-	1.75	2.20	
	V <sub>CE</sub> (sat)		Tj=125°C	-	2.05	-	
	(chip)		Tj=150°C	-	2.10	-	
Internal gate resistance	R <sub>g(int)</sub>	-		-	1.75	-	Ω
Input capacitance	Cies	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 1MHz		-	55	-	nF
Input capacitance  Turn-on time	ton	$V_{\rm CC} = 600V$ $I_{\rm C} = 600A$ $V_{\rm GE} = \pm 15V$ $R_{\rm G} = 2.4\Omega$ Ls=70nH		-	1.00	-	µsec
	tr			-	0.40	-	
	tr (i)			-	0.15	-	
Turn-off time	toff			-	1.20	-	
	tf			-	0.15	-	
Forward on voltage	V <sub>F</sub>		Tj=25°C	-	1.80	2.25	V
	(terminal)		Tj=125°C	-	1.95	-	
	(*4)	V <sub>GE</sub> = 0V I <sub>F</sub> = 600A	Tj=150°C	-	1.90	-	
	· /		Tj=25°C	-	1.70	2.15	
	V <sub>F</sub>		Tj=125°C	-	1.85	-	
	(chip)		Tj=150°C	-	1.80	-	
Reverse recovery time	trr	I <sub>F</sub> = 600A		-	0.20	-	µsec
Resistance B value		T=25°C		-	5000	-	Ω
	R	T=100°C		465	495	520	
B value	В	T=25/50°C		3305	3375	3450	K

Note \*4: Please refer to page 6, there is definition of on-state voltage at terminal.

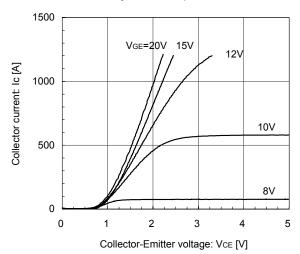
#### Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
items		Conditions	min.	typ.	max.	Units
Thermal resistance (1device)	Rth(j-c)	Inverter IGBT	-	-	0.045	°C/W
		Inverter FWD	-	-	0.075	
Contact thermal resistance (1device) (*5)	Rth(c-f)	with Thermal Compound	-	0.0125	-	

#### **■** Characteristics (Representative)

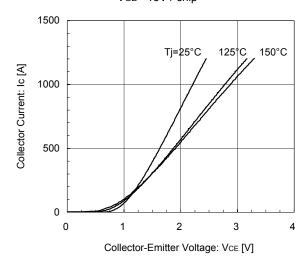
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Tj= 25°C / chip



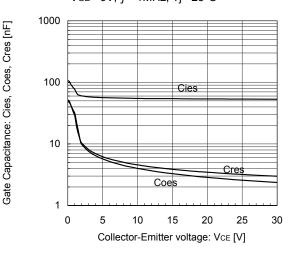
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) VGE= 15V / chip



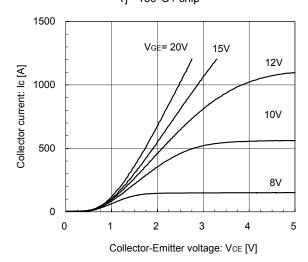
[INVERTER]

Gate Capacitance vs. Collector-Emitter Voltage (typ.)  $V_{GE} = 0V$ , f = 1MHz,  $T_{J} = 25^{\circ}C$ 



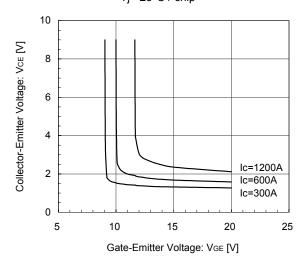
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Tj= 150°C / chip



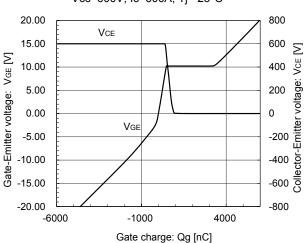
[INVERTER]

Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)  $T_j = 25$ °C / chip



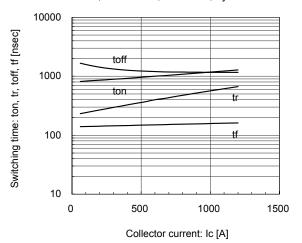
[INVERTER]

Dynamic Gate Charge (typ.) Vcc=600V, Ic=600A, Tj= 25°C



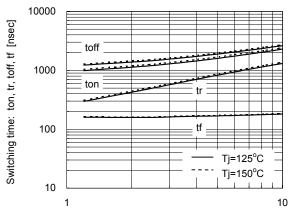
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=600V, VgE= $\pm$ 15V, Rg=2.4 $\Omega$ , Tj=25 $^{\circ}$ C



[INVERTER]

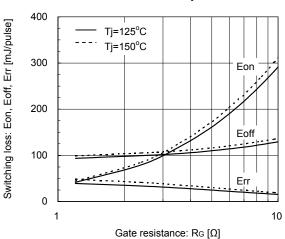
Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=600A, VgE=±15V, Tj=125°C, 150°C



Gate resistance: Rg  $[\Omega]$ 

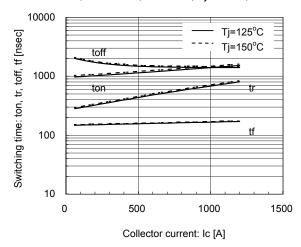
[INVERTER]

Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=600A, VGE= $\pm$ 15V, Tj=125°C, 150°C



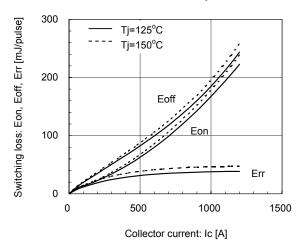
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=600V, VgE= $\pm$ 15V, Rg= $2.4\Omega$ , Tj=125°C, 150°C



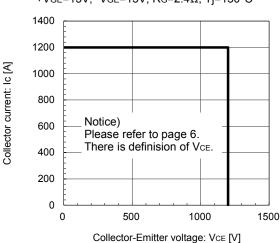
[INVERTER]

Switching loss vs. Collector current (typ.) Vcc=600V , VgE= $\pm$ 15V, Rg=2.4 $\Omega$ , Tj=125°C, 150°C



[INVERTER]

Reverse bias safe operating area (max.) +VGE=15V, -VGE=15V, RG=2.4 $\Omega$ , Tj=150°C



[INVERTER] Forward Current vs. Forward Voltage (typ.) chip 1500 Tj=25°C Forward current: IF [A] 1000 125°C 500 150°0 0 0 3

2 Forward on voltage: VF [V]

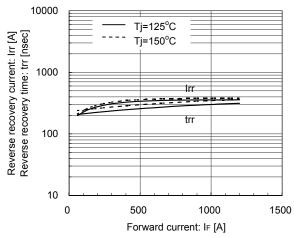
Vcc=600V, VgE= $\pm$ 15V, Rg=2.4 $\Omega$ , Tj=25 $^{\circ}$ C 10000 Reverse recovery current: Irr [A] Reverse recovery time: trr [nsec] 1000 Irr 100 10 0 500 1000 1500

Forward current: IF [A]

[INVERTER]

Reverse Recovery Characteristics (typ.)

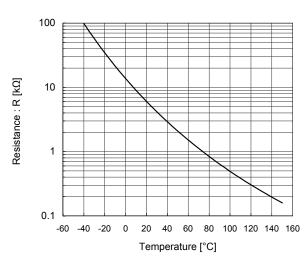
[INVERTER] Reverse Recovery Characteristics (typ.) Vcc=600V, VgE=±15V, Rg=2.4Ω, Tj=125°C, 150°C 10000



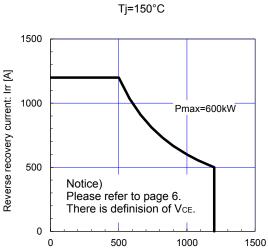
Transient Thermal Resistance (max.) 1 Thermal resistanse: Rth(j-c) [°C/W] **FWD** 0.1 **IGBT** 0.01 0.001 0.0301 0.0001 0.001 Pulse Width: Pw [sec]

[THERMISTOR]

Temperature characteristic (typ.)

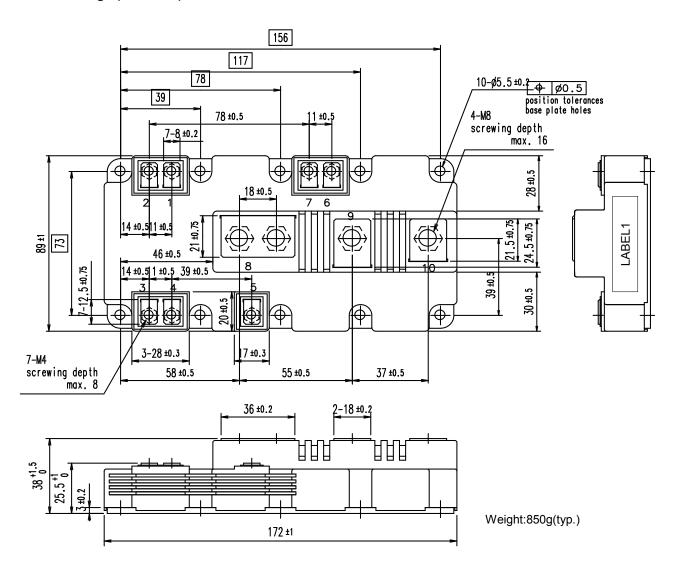


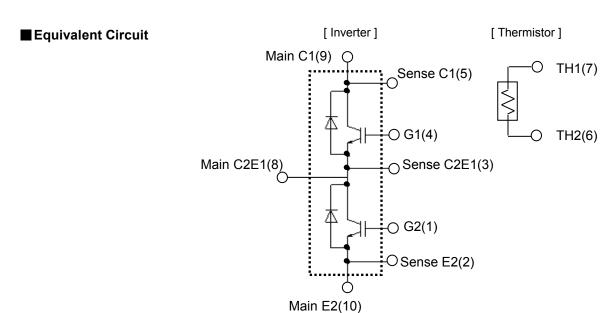
FWD safe operating area (max.)



Collector-Emitter voltage: VcE [V]

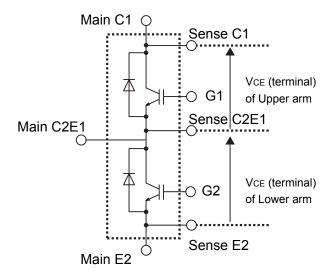
#### ■ Outline Drawings (Unit: mm)





http://www.fujielectric.com/products/semiconductor/

### ■ Definition of on-state voltage at terminal and switching characteristics



Fuji defined VcE value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm.

Switching characteristics of VcE also is defined between Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Please use these terminals whenever measure spike voltage and on-state voltage .

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- Communications equipment (terminal devices)
- Measurement equipment

- · Machine tools
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- Personal equipment Industrial robots etc.

· Gas leakage detectors with an auto-shut-off feature

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· Safety devices

Trunk communications equipment

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